

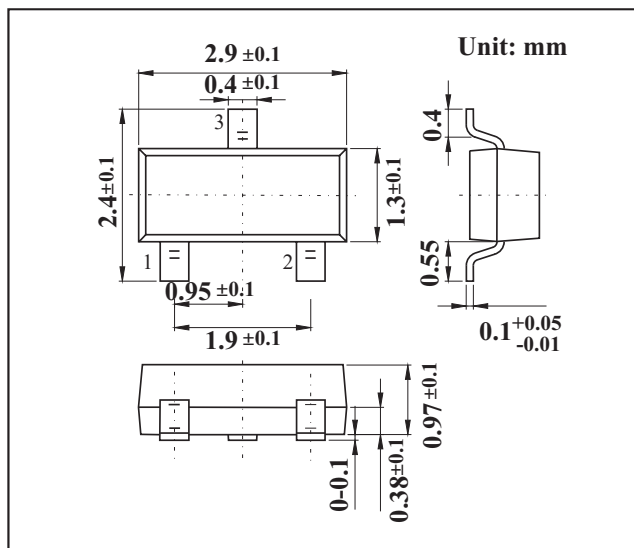
SOT-23 Plastic-Encapsulate Transistors

Features

- Collector current: $I_C=0.5A$
- Weight:0.080 grams(approx)
- PNP Transistors

MECHANICAL DATA

- Case style:SOT-23molded plastic
- Mounting position:any



MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Parameter	Symbol	Rating	Unit
Collector-Base Voltage	V_{CBO}	-40	V
Collector-Emitter Voltage	V_{CEO}	-25	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current -Continuous	I_C	-0.5	A
Collector Power Dissipation	P_C	0.3	W
Junction Temperature	T_j	150	°C
Storage Temperature	T_{stg}	-55 to 150	°C

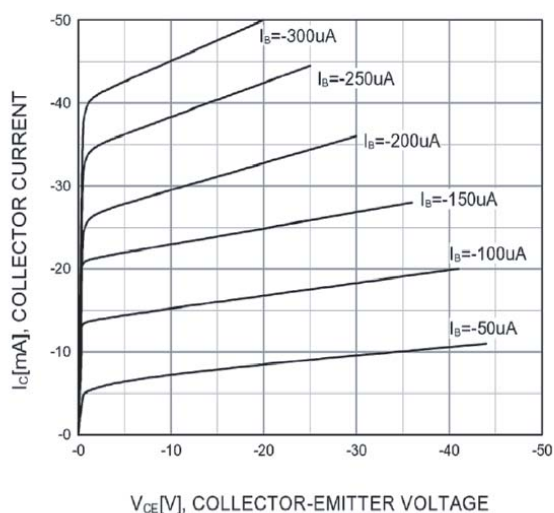
Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V_{CBO}	$I_C=-100\mu A, I_E=0$	-40			V
Collector-emitter breakdown voltage	V_{CEO}	$I_C=-1mA, I_B=0$	-25			V
Emitter-base breakdown voltage	V_{EBO}	$I_E=-100\mu A, I_C=0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB}=-40V, I_E=0$			-0.1	μA
Collector cut-off current	I_{CEO}	$V_{CE}=-20V, I_B=0$			-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=-3V, I_C=0$			-0.1	μA
DC current gain	h_{FE}	$V_{CE}=-1V, I_C=-50mA$	200		350	
		$V_{CE}=-1V, I_C=-500mA$	50			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-500mA, I_B=-50mA$			-0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=-500mA, I_B=-50mA$			-1.2	V
Transition frequency	f_T	$V_{CE}=-6V, I_C=-20mA, f=30MHz$	150			MHz

Marking

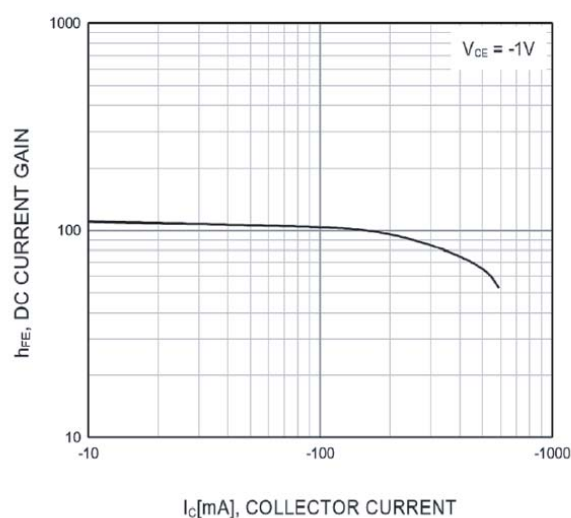
Marking	2TY
---------	-----

RATINGS AND CHARACTERISTIC CURVES

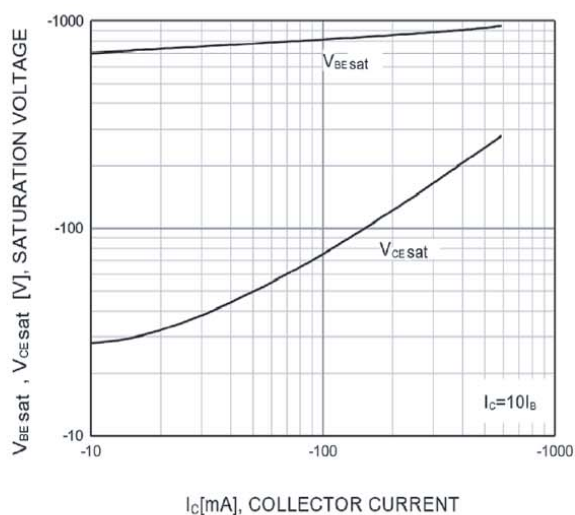
■ Typical Characteristics



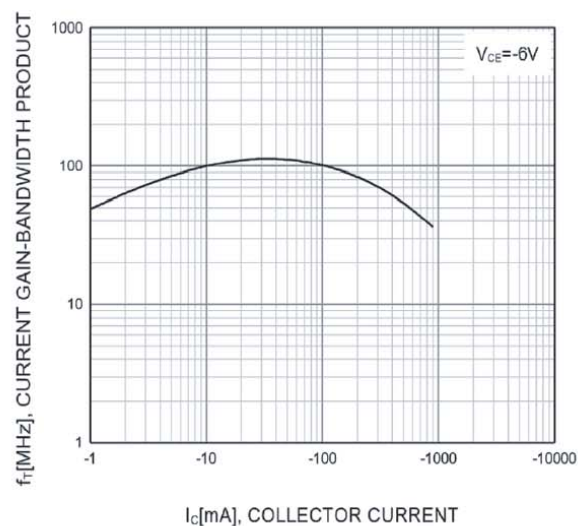
Static Characteristic



DC current Gain



Base-Emitter Saturation Voltage
Collector-Emitter Saturation Voltage



Current Gain Bandwidth Product